



# isc Silicon PNP Power Transistor

## **DESCRIPTION**

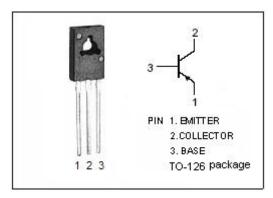
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -40V (Min)
- · Good Linearity of hFE
- Complement to Type 2SC3422
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

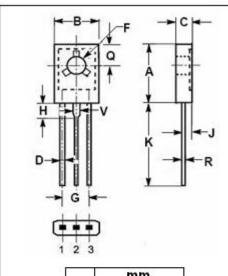
### **APPLICATIONS**

 Designed for audio frequency power amplifier and low speed switching applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-40	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V	
Ic	Collector Current-Continuous	-3	А	
I <sub>B</sub>	Base Current-Continuous	-1	А	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	1.5	10/	
Pc	Total Power Dissipation @ T <sub>C</sub> =25℃	10 W		
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C	





- 4	mm	
DIM	MIN	MAX
Α	10.70	10.95
В	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
Н	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37



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2SA1359

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-40			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-0.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-0.1	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-0.1	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	80		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2.5A; V <sub>CE</sub> = -2V	25			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V		100		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1.0MHz		35		pF

## ♦ h<sub>FE-1</sub> Classifications

0	Y	
80-160	120-240	

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